

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Page 1, lines 1-5 (the first paragraph on page 1): please replace this paragraph with the following rewritten paragraph:

A<sub>1</sub>  
This application is related to U.S. Patent ~~Application No. \_\_\_\_\_~~ (Attorney Docket No. ~~LAM2P256~~) No. 6,541,361, filed on the same day as the instant application and entitled "PLASMA ENHANCED METHOD FOR INCREASING SILICON-CONTAINING PHOTORESIST SELECTIVITY." This application is hereby incorporated by reference.

Page 7, line 8 (the brief description for Figure 2): please replace this paragraph with the following rewritten paragraph:

A<sub>2</sub>  
Figure 2 ~~illustrate~~ illustrates a block diagram depicting a developed substrate.

Page 12, lines 7-14 (the first full paragraph on page 12): please replace this paragraph with the following rewritten paragraph:

A<sub>3</sub>  
In a preferred embodiment of the invention as illustrated in Figure ~~5~~ 3, the top layer 110 of silicon-containing photoresist has a thickness of about 2000 Å while the bottom layer 116 of non silicon-containing photoresist has a thickness of about 6000 Å. In a general embodiment, the silicon-containing photoresist has a thickness that ranges between 1000 Å and about 3000 Å, while the bottom layer 116 of non silicon-containing photoresist has a thickness that ranges between about 3000 Å and about 8000 Å. In

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A3  
cont.  
another embodiment of the invention, the cross-linked layer 138 has a thickness between  
about 5% to about 75% of the thickness of the original layer 110.

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